DIELECTRIC PROPERTIES OF Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{1-x}Ce_xO₃ CERAMICS OBTAINED BY THE PEROXOMETHOD

S. Andreev ^a, <u>P. Petkov</u>^b

^aInstitute of Solid State Physics, Bulgarian Academy of Sciences, 72 Tzarigradsko Chaussee Blvd., 1784 Sofia, Bulgaria, E-mail: sandreev@issp.bas.bg University of Chemical Technology and Metallurgy 8 Kl. Ohridski, 1756 Sofia, Bulgaria E-mail: p.petkov@uctm.edu Received 14 February 2006 Accepted 20 February 2006

ABSTRACT

The samples of the system $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{1.x}Ce_xO_3$ are synthesized by the peroxomethod with x = 0.025, 0.050, 0.075 and 0.100 mol at calcination temperatures $T_{cal} = 1300$, 1350 and 1400 °C and calcination time 2.5 h. The following important dielectric properties of the system are investigated at frequency of 1 kHz: permitivity ε_r , dielecric losses tan δ and conductivity σ . At increasing the concentration of CeO₂ the dielectric constant ε_r is reduced but the thermal stability of the capacitors investigated is improved. The composition $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.925}Ce_{0.075}O_3$ demonstrates a zero temperature coefficient of the dielectric constant $TC\varepsilon_r = 0$ and tan $\delta = 58x10^4$.

<u>Keywords</u>: dielectric properties, $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{1-x}Ce_xO_3$.

INTRODUCTION

Multicomponent metatitanates are of a definite practical interest because they offer the possibility for controlled variations of the parameters of passive electronic components. Perovskyte type $BaTiO_3$ ceramics are one of the most important electronic materials for use in multilayer ceramic capacitors, positive temperature coefficient thermistors and piezoelectric tranducers [1-5]. More importantly, the electrical conductivity of $BaTiO_3$ system ceramics can be controlled by minor modifications of dotents or variation of sintering conditions without seriously affecting other properties; ranges from ferroelectricity to semiconductivity [6]. Materials suitable for manufacturing of thermostable capacitors with low dielectric losses are investigated in this work. Such materials based on the systems BaTiO₃-MgTiO₃ [7-9], (Ba,Sr)TiO₃ [10-12] and (Ba,Sr,Mg)TiO₃ [13] are discussed in the literature and they demonstrate valuable characteristics. The main intent of this work is the investigation of ceramic materials on the base of Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{1-x}Ce_xO₃ applicable for the production of thermal stability capacitors with low dielectric losses. However no data are reported about the possible depressor behavior of CeO₂ included in such systems. It is assumed that introducing CeO₂ into the starting material (Ba,Sr,Mg)TiO₃ would result in smoothening of the temperature-dependence maximum of ε_r around the Curie temperature and in reduction of the dielectric losses.

EXPERIMENTAL

In this work the metatitanates of Ba^{2+} , Sr^{2+} and Mg^{2+} are obtained by the peroxomethod [14-17], as described by the following equation:

 $TiCl_4 + Me^{2+} + H_2O_2 + OH^{\cdot} + H_2O \rightarrow Me_2Ti_2(OH)_x(O_2)_y(H_2O)_z \rightarrow MeTiO_3 + O_2 + H_2O$

 H_2O_2 is added to a solution of TiCl₄ and a Mesalt (Me-Ba²⁺, Sr²⁺, Mg²⁺). Then the solution is alkalized with NH_4OH to pH = 9 and 12. The synthesized peroxocompositions are calcined at temperatures of 600 °C and 650 °C respectively, upto obtaining metatitanates with grain size under 1µm. BaTiO₂, SrTiO₂ and MgTiO3 are identified by X-ray analysis [18-20], with a TUR-62 apparatus. CeO, is of 99.0 % purity. The following compositions: $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{1-x}Ce_{x}O_{3}$, where x = 0.025, 0.050, 0.075 and 0.100 mol are synthesized. The powders obtained are homogenized in a planetary ball mill for 30 min. They are pressed at a pressure $P = 150 \times 10^5 Pa$. 10 % polyvinyl alcohol is used as a binder. Pellets with diameter of 9 mm and thickness of 4 mm are obtained. They are calcined at $T_{cal} = 1300$, 1350 and 1400°C for 2.5 h. At $T = 360^{\circ}C$ the temperature was maintained constant for 0.5 h in order to achieve a gradual evaporation of the binder. The pellets are metalized on both sides by means of a silver paste.

The capacitance C and the dielectric losses are measured at a frequency of 1 kHz on a General Radio 1687 system. The temperature dependence of the capacitance C and the dielectric losses is investigated with an Heraeus Votsh temperature chamber. The resistance is measured on a Terohm meter TR-2201 at a voltage of 50 V applied.

RESULTS AND DISCUSSION

The dependence of the permittivity on the composition of the system (x) and the calcination temperature T_{cal} , observed at $T = 20^{\circ}$ C, is shown in Figure 1. It is seen from the Figure that at $T = 20^{\circ}$ C, ε_r of the samples strongly depends on the composition and to some lower degre on the temperature T_{cal} . ε_r has it's a maximum value at x = 0.025 mol. It falls down at greater values of x. This could be explained by the enhanced concentration of CeO₂ featuring lower ε_r . It is seen also from Figure 1 that ε_r (measured at 20°C) is increasing



Fig. 1 Dependence of the permittivity ε_r on the composition x mol at three different calcinations temperatures ($T_{cal.} = 1300$, 1350 and 1400 °C).



Fig. 2. Dependence of the dielectric losses tan δ on the composition x mol at three different calcinations temperatures (T_{cal} = 1300, 1350 and 1400 °C).

with higher $T_{cal.}$ and for x = 0.025 mol, $T_{cal.}$ = 1400°C the value of ε_r is 1200 (for the same x = 0.025 mol and $T_{cal.}$ = 1300°C, ε_r = 920. This behavior could be explained by the higher degree of formation of the isomorphic structure and the higher density of the ceramics ($\rho_{1300^{\circ}C}$ = 5000 kg m⁻³ for the composition $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.975}Ce_{0.025}O_3$). It is seen from the figure that the $T_{cal.}$ = 1300 °C is not high enough for formation of a domain structure.

In Figure 2 the dependence of the dielectric losses tan δ on x and T_{cal} is illustrated. Dielectric losses in-



Fig. 3. Temperature dependence of the permittivity $\epsilon_{\rm r}~(1\text{-}x=0.025$ mol, 2-x = 0.050 mol, 3-x = 0.075 mol, 4-x = 0.100 mol).



Fig. 4 Temperature dependence of the conductivity $lg\sigma$ (1- $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.950}Ce_{0.025}O_3,\ 2$ - $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.950}Ce_{0.050}O_3,\ 3$ - $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.900}Ce_{0.100}O_3$)

crease at greater concentrations of CeO₂ in the samples. For composition x = 0.025 mol tan $\delta = 30x10^{-4}$ and for x = 0.100 mol tan $\delta = 65x10^{-4}$. As a reference the pure composition Ba_{0.5}Sr_{0.3}Mg_{0.2}TiO₃ (1400°C) features tan $\delta = 37x10^{-4}$ [13]. Increasing of tan δ at higher T_{cal} is also observed. A probable reason for this is the higher concentration of defects in the crystal lattice at T_{cal} = 1400°C.

The temperature dependence of $\varepsilon_{\rm r}$ at $T_{\rm cal.}$ = 1400°C and at different compositions x is represented in Figure 3. At higher concentrations of CeO, the maxi-

mum of this dependence is smoothed resulting in higher temperature stability of the capacitors. At x = 0.075 mol the permittivity has a constant value in the range - $40 \div 120^{\circ}$ C (TC $\mathcal{E}_r = 0$).

From the experimental data represented above a conclusion may be drawn that the ceramic material with composition $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.925}Ce_{0.075}O_3$ produced at $T_{cal.} = 1400$ °C demonstrates a zero temperature coeficient (TC $\mathcal{E}_r = 0$) and low enough dielectric losses (tan $\delta = 58 \times 10^{-4}$), within an wide temperature range (-40÷120°C). This material could be used successfully for the production of thermostable capacitors with low dielectric losses.

In Fig. 4 the temperature dependence of the measured conductivity σ of the materials investigated is represented in a logarithmic scale. As it is seen from Fig. 4 each of the curves describing the temperature dependence of σ in a logarithmic scale consists of two linear parts corresponding to different activation energies (ΔE). For the compositions Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.95}Ce_{0.05}O₃ and Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.925}Ce_{0.075}O₃ the activation energies within the temperature range 20 – 100°C are 0.28 eV and 0.36 eV respectively. Within the higher temperature range 100 – 200 °C these energies are 0.96 eV and 1.21 eV. For the composition Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.9}Ce_{0.1}O₃ the activation energy for the range 20 – 80 °C is 0.9 eV and for the range 80 – 200°C – it is 1.48 eV.

These energies correspond to an impurity character of the conductivity. In the lower-temperature range the conductivity is limited mainly by the interlayers between the grains (crystallites) while in the higher-temperature range it is determined by the intrinsic defects. Predominant are oxygen vacancies created during the high temperature calcination of the materials. These defects are compensated electrically by lowering the degree of oxidation of the nearest-neighbor ions [21].

CONCLUSIONS

Samples of the system $Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{1-x}Ce_xO_3$ are synthesized by the peroxomethod with x=0.025, 0.050, 0.075 and 0.100 mol at calcination temperatures $T_{cal.} = 1300, 1350$ and 1400°C and calcination time 2.5 h.

At increasing the concentration of CeO_2 the stability of the produced sample capacitors is improved but this improvement goes together with lower values of \mathcal{E}_{r} and higher values of tan δ . A successful trade-off is the composition Ba_{0.5}Sr_{0.3}Mg_{0.2}Ti_{0.925}Ce_{0.075}O₃ with TC $\mathcal{E}_{r} = 0$ and low dielectric losses, tan $\delta = 58\times10^{-4}$. Due to these parameters this material could be applied successfully in the production of thermally stable capacitors with low dielectric losses.

REFERENCES

- Gs.Wang, Jg. Cheng, Xj. Meng, J. Yu, Zq. Lai, J. Tang, Sl. Guo, Jh. Chu, G. Li, Qh. Lu, Appl. Phys. Lett., 78, 2001, 4172-4174.
- D. Xie, W. Pan, H. Shi, Rare Metal Mater. Engin., 31, 2002, 331-334.
- M. Fukunaga, Gb. Li, Y. Uesu, K. Kohn, Ferroelectrics, 286, 2003,801-806.
- 4. Rg., Mendes, J. Eiras, J. Europ. Ceram. Soc., 24, 1637-1640.
- D. Xie, W. Pan, H.Shi, Mater. Sci. Engin. B-Solid State Mater. Advan. Technol., 99, 2003, 352-355.
- V. Vassilev, Annual Proceedings Techn. Univ. Varna, 4, 2004, 171-175.
- 7. K. Okadzaki, Tehnologya Keramicheskih Dielektrikov, Energiya, Moskva, (1976), (in Russian).

- 8. V. Gurevich, Electroprovodnost Segnetoelektrikov, Komitet standartov, Moscow, 1989, (in Russian).
- V. Parvanova, J. Univ. Chem. Technol. Met. (Sofia), 37, 4, 2002 13-18.
- Mendes, R., J. Eiras, Integrated ferroelectrics, 58, 2003, 1395-1398.
- Liqin Zhong, Zhihna Jiang, Shuren Zhang, Changkui Yn. J. Mat. Sci. Lett., **11**, 16, 1992, 1134-1139.
- V. Parvanova, J. Univ. Chem. Technol. Met. (Sofia), 37, 3, 2002, 5-10.
- V. Parvanova, J. Univ. Chem. Technol. Met. (Sofia), 38, 1, 2003, 23-30.
- 14. Pat. Jap. 'H 51-80 Cl. C 01 G 23/00, (in Japanes).
- 15 L. Genov, M. Maneva, V. Parvanova, J. Therm. Anal., 33, 1988, 727-734.
- 16. M. Maneva, V. Parvanova, J. Therm. Anal., 41, 1995, 353-361.
- V. Parvanova, M. Maneva, Termochim. Acta, 279, 1996, 137-141.
- 18. JCPDS-05-0626.
- 19. JCPDS-35-0734.
- 20. JCPDS-06-0494.
- 21. J. Poplavko, Fizika Dielektrikov, Vissha Shkola, Kiev, 1980, (in Russian).